



Enhancing Thermoelectric Performance of Half-Heusler Compounds via Nanostructuring Approaches



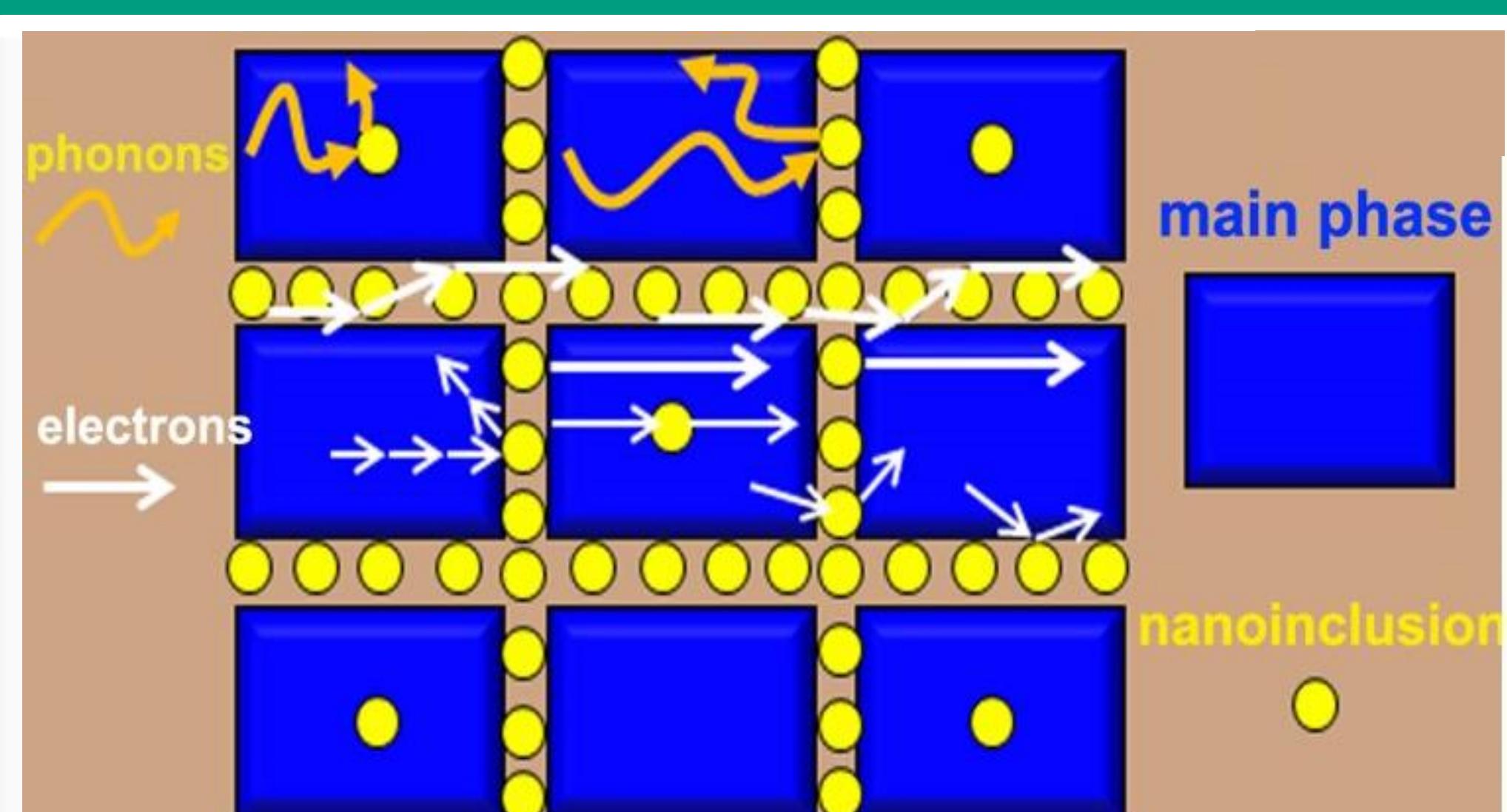
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Introduction

Half-Heusler compounds have attracted considerable interest as promising thermoelectric (TE) materials in the temperature range around 700 K and above, which is close to the temperature range of most industrial waste heat sources. In this poster, we summarize our recent progress in improving the thermoelectric performance of half-Heusler compounds via nanostructuring approaches. We successfully utilized nanostructuring approaches to decouple thermal and electrical transport properties in half-Heusler compounds. By controlling the *in-situ* formation of InSb [1-2], MnSb [3] and full-Heusler nanoinclusions [4] in the half-Heusler matrix, it was shown experimentally that the Seebeck coefficient (α), electrical conductivity (σ) and thermal conductivity (κ) can be independently manipulated in a manner that significantly enhances the figure of merit (ZT) of these materials.

Graphical Abstract

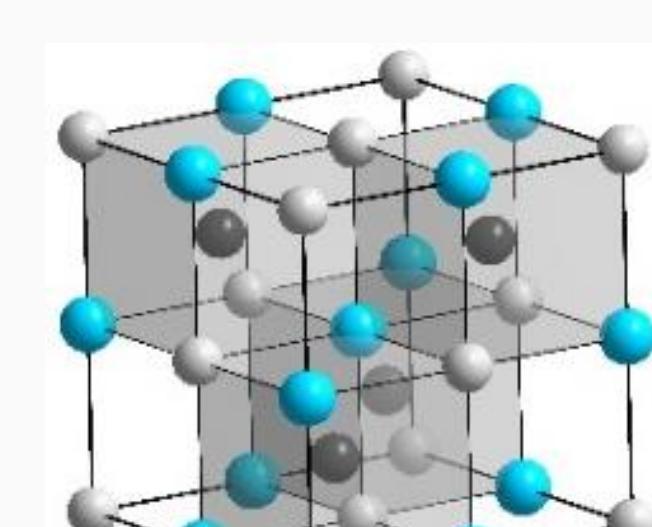


The roles of nanoinclusions (NI)

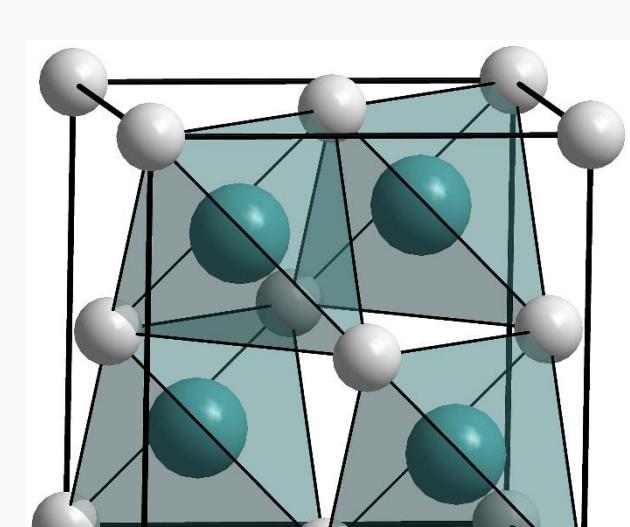
- 1) Electron filtering effect → $\alpha \uparrow$
- 2) Electron injection effect → $\sigma \uparrow$
- 3) Boundary scattering of phonons → $\kappa \downarrow$

The *in-situ* formed nanoinclusions in half-Heusler compounds can induce combined *high mobility electron injection* (thick long arrow), *low energy electron filtering* (narrow short arrow), and *boundary scattering* (wavy arrow) effects, and lead to a simultaneous improvement of all three individual thermoelectric properties of half-Heusler nanocomposites.

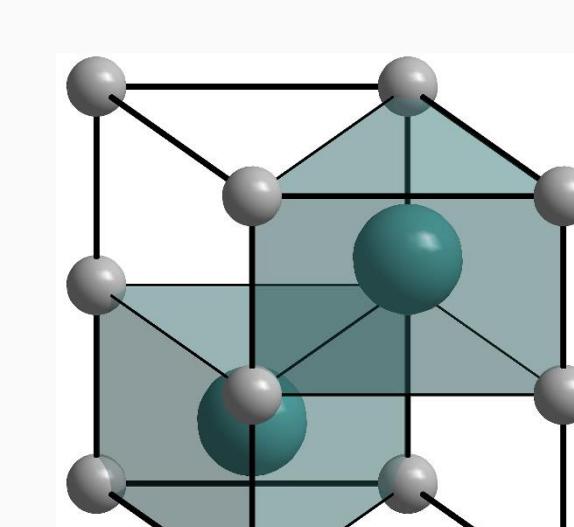
Building Blocks



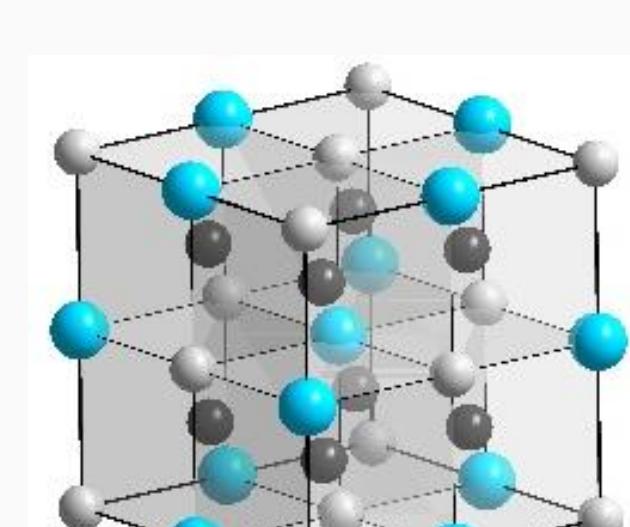
half-Heusler



InSb (NI)

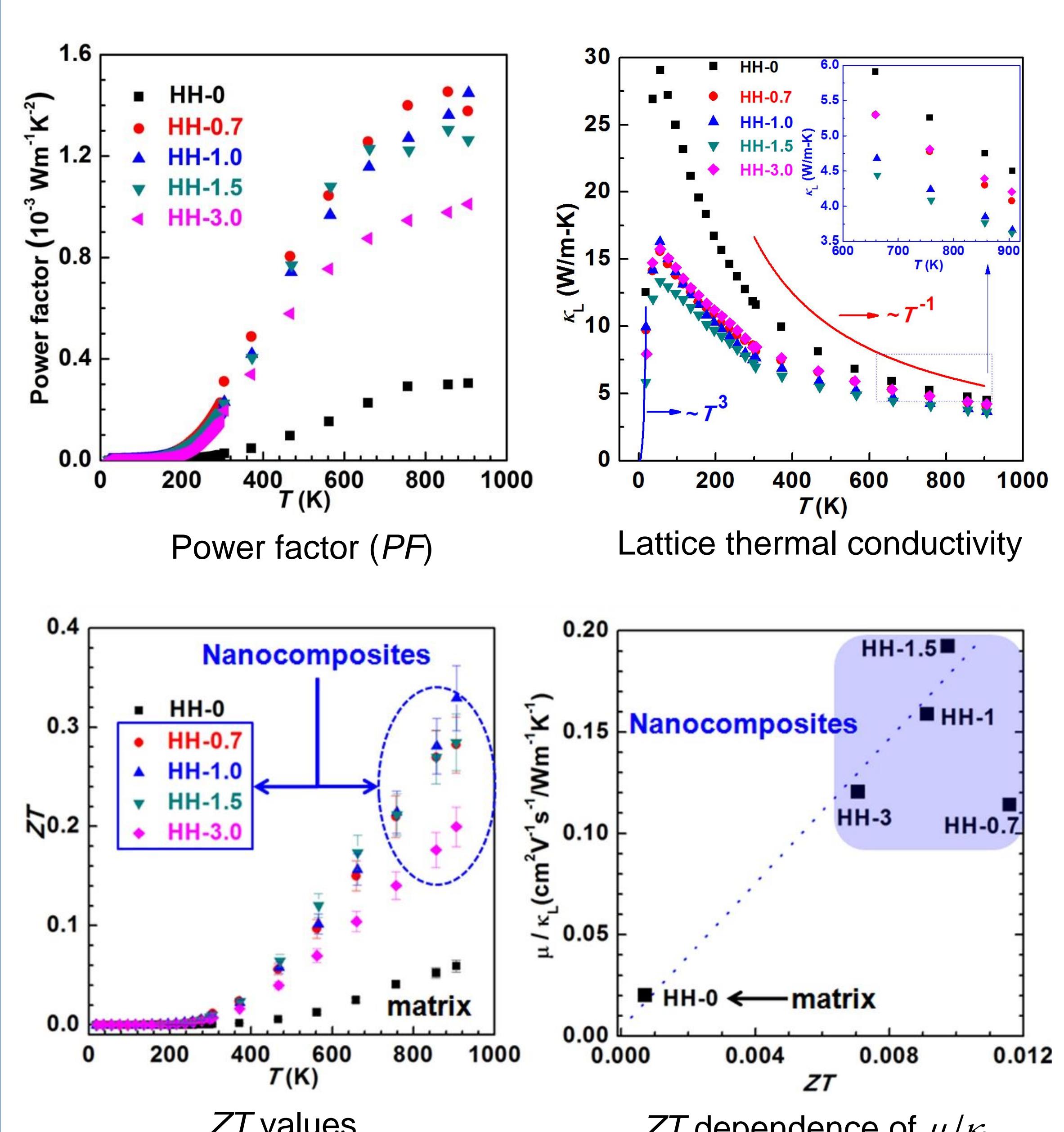
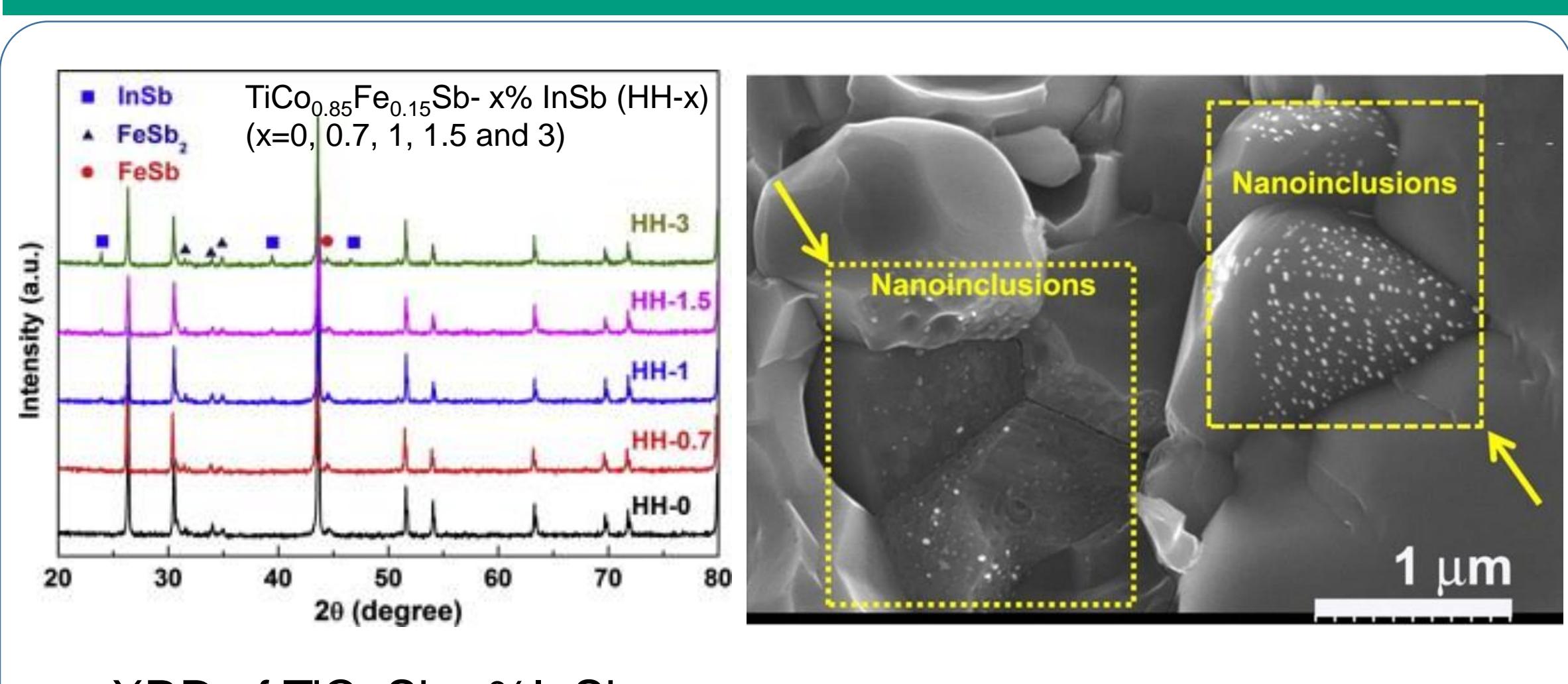


MnSb (NI)

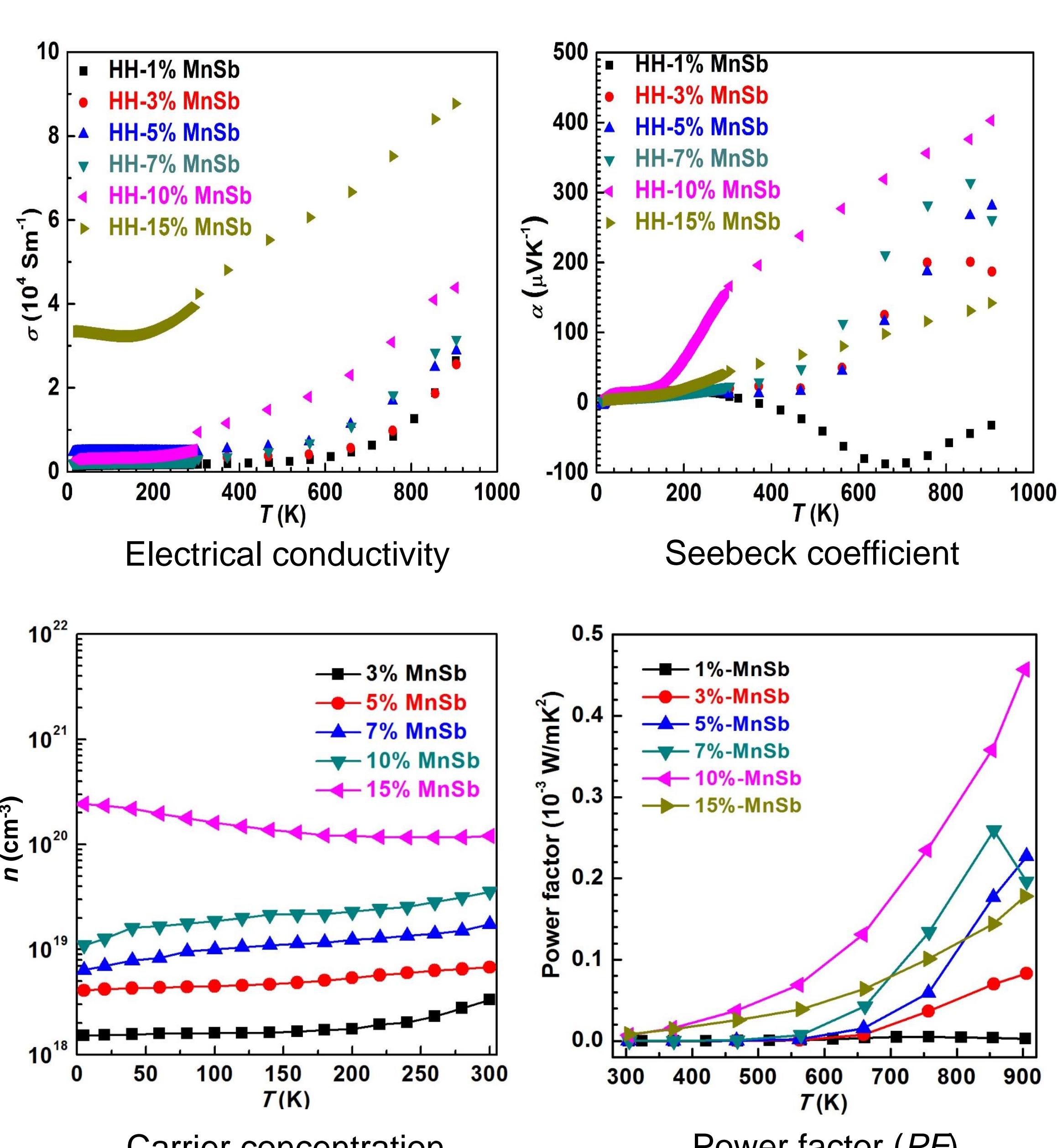
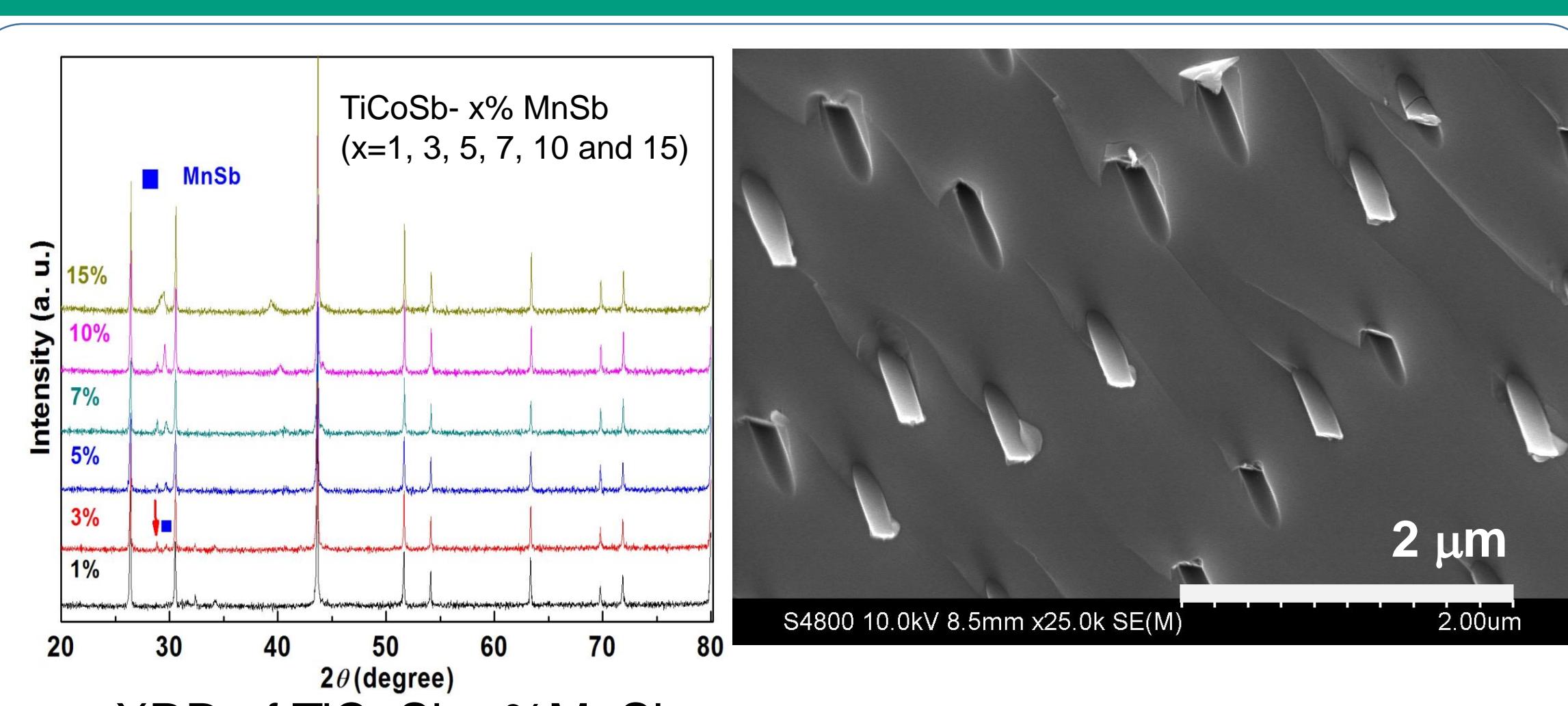


full-Heusler (NI)

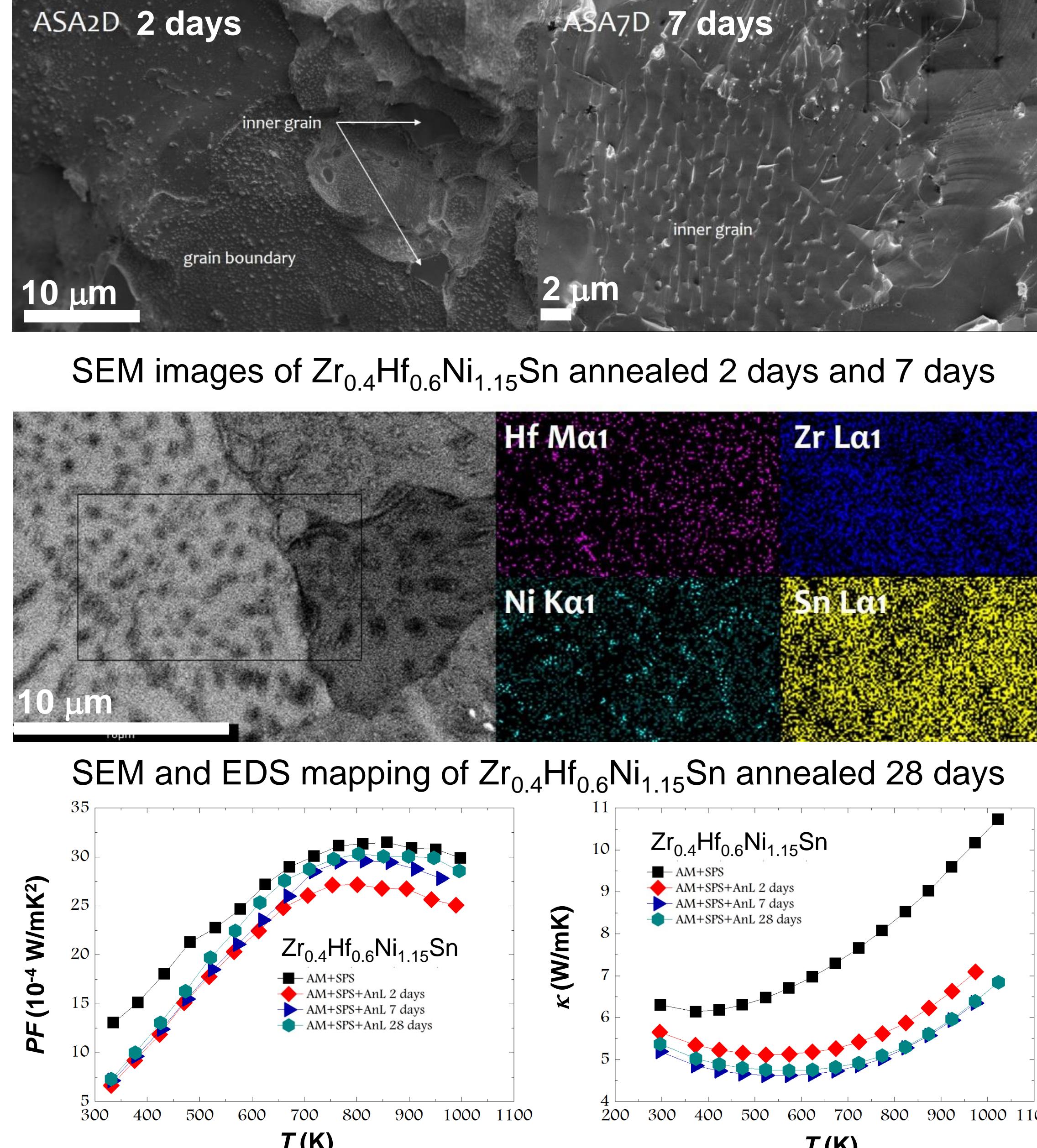
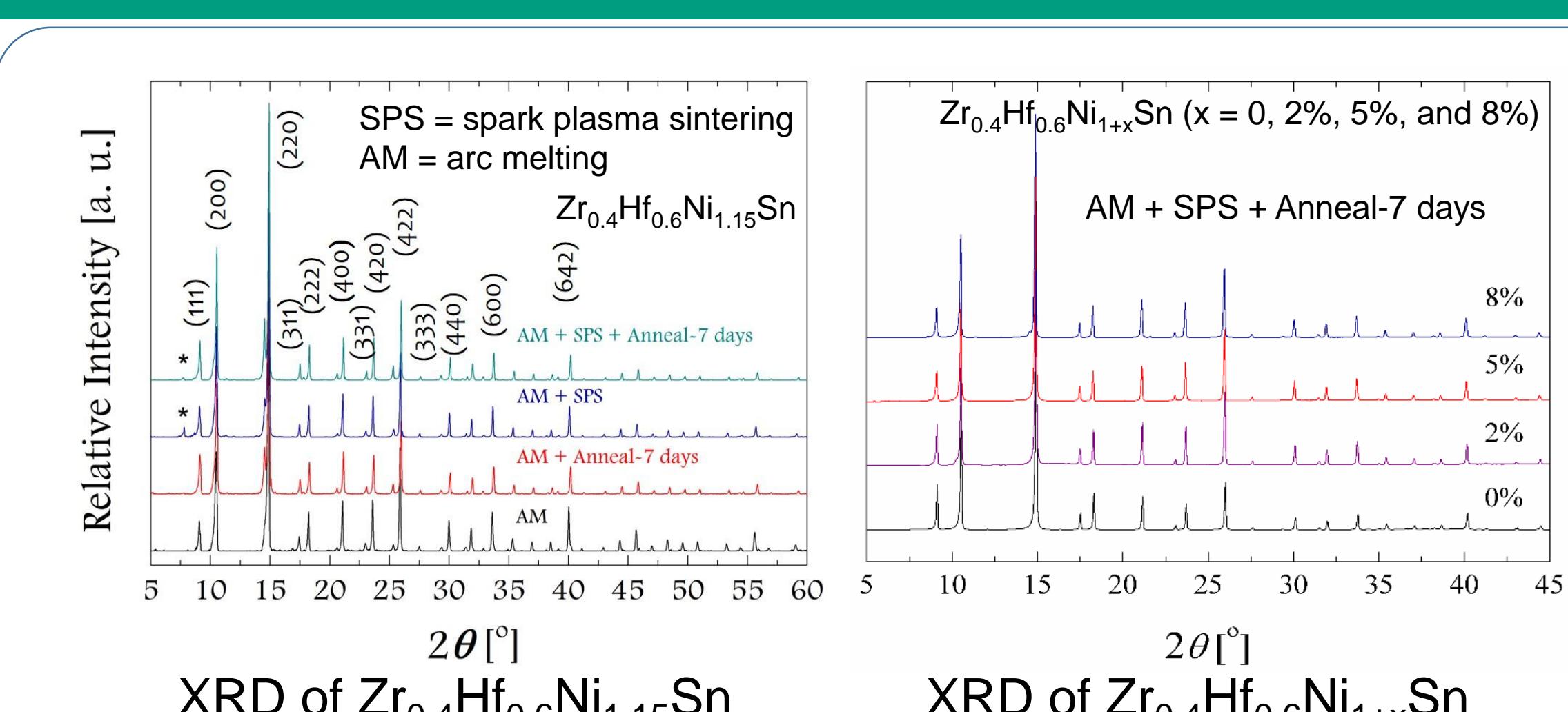
TiCo_{0.85}Fe_{0.15}Sb-InSb



TiCoSb-MnSb



Zr_{0.4}Hf_{0.6}Ni_{1+x}Sn



Checklist:

- 1) Electron filtering effect → $\alpha \uparrow$ ✓
- 2) Electron injection effect → $\sigma \uparrow$ ✓
- 3) Boundary scattering of phonons → $\kappa \downarrow$ ✓

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- 2) Electron injection effect → $\sigma \uparrow$ ✗
- 3) Boundary scattering of phonons → $\kappa \downarrow$ ✓

References

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